

# Hazem K Khanfar

## List of Publications by Year in descending order

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#	ARTICLE	IF	CITATIONS
1	Preparation and Characterization of Orthorhombic AgMn Alloys by the Pulsed Laser Welding Technique. <i>Crystal Research and Technology</i> , 2022, 57, .	1.3	6
2	Band offsets, dielectric dispersion and some applications of CdSe/GeO <sub>2</sub> heterojunctions. <i>Optik</i> , 2021, 231, 166506.	2.9	9
3	Al/MoO <sub>3</sub> /ZnPc/Al Broken Gap Tunneling Hybrid Devices Design for IR Laser Sensing and Microwave Filtering. <i>IEEE Sensors Journal</i> , 2020, 20, 14772-14779.	4.7	12
4	Design and Characterization of MoO <sub>3</sub> /Mg/MoO <sub>3</sub> Interfaces. <i>IEEE Transactions on Electron Devices</i> , 2020, 67, 4354-4359.	3.0	7
5	Optical dynamics at the MoO <sub>3</sub> /ZnPc interfaces prepared for visible light communications. <i>Physica Scripta</i> , 2020, 95, 075503.	2.5	7
6	Structural and electrical characterizations of the as grown and annealed Au/M <sub>1</sub> O <sub>3</sub> /In/MoO <sub>3</sub> /C bandpass filters. <i>Microwave and Optical Technology Letters</i> , 2019, 61, 2866-2872.	1.4	3
7	Post annealing effects on the structural and optical properties of MoO <sub>3</sub> sandwiched with indium slabs. <i>Materials Research Express</i> , 2019, 6, 116453.	1.6	0
8	Formation Mechanism, Structural and Optoelectronic Properties of As <sub>2</sub> Se <sub>3</sub> /CdS Heterojunctions Prepared by Physical Vapor Deposition Technique. <i>Journal of Electronic Materials</i> , 2019, 48, 4368-4374.	2.2	4
9	Enhancement of the performance of the Cu <sub>2</sub> Se band filters via Yb nanosandwiching. <i>Microwave and Optical Technology Letters</i> , 2019, 61, 1449-1455.	1.4	2
10	Negative Capacitance Effect in Ag/In <sub>2</sub> Se <sub>3</sub> /CdS/CdSe/C Dual Band Stop Filters. <i>Journal of Electronic Materials</i> , 2019, 48, 244-251.	2.2	6
11	Design and electrical performance of CdS/Sb <sub>2</sub> Te <sub>3</sub> tunneling heterojunction devices. <i>Materials Research Express</i> , 2018, 5, 026303.	1.6	36
12	Impact of Mg layer thickness on the performance of the Mg/Bi <sub>2</sub> O <sub>3</sub> plasmonic interfaces. <i>Thin Solid Films</i> , 2018, 651, 71-76.	1.8	4
13	Design and characterization of Au/In <sub>4</sub> Se <sub>3</sub> /Ga <sub>2</sub> S <sub>3</sub> /C field effect transistors. <i>Results in Physics</i> , 2018, 8, 1239-1244.	4.1	8
14	Characterization of CdS/Sb <sub>2</sub> Te <sub>3</sub> micro/nano-interfaces. <i>Optik</i> , 2018, 158, 1154-1159.	2.9	5
15	Optoelectronic properties of the InSe/Ga <sub>2</sub> S <sub>3</sub> interfaces. <i>Results in Physics</i> , 2018, 10, 332-338.	4.1	5
16	Design and Performance of (Au,Yb)/ZnS/InSe/C Heterojunctions as Plasmon Resonators, Photodetectors and Microwave Cavities. <i>Journal of Electronic Materials</i> , 2017, 46, 1650-1657.	2.2	7
17	Design and Applications of Yb/Ga <sub>2</sub> Se <sub>3</sub> /C Schottky Barriers. <i>IEEE Sensors Journal</i> , 2017, 17, 4429-4434.	4.7	18
18	Impact of Yb, In, Ag and Au thin film substrates on the crystalline nature, Schottky barrier formation and microwave trapping properties of Bi <sub>2</sub> O <sub>3</sub> films. <i>Materials Science in Semiconductor Processing</i> , 2017, 64, 63-70.	4.0	20

#	ARTICLE	IF	CITATIONS
19	Microwave Impedance Spectroscopy and Temperature Effects on the Electrical Properties of Au/BN/C Interfaces. <i>Active and Passive Electronic Components</i> , 2017, 2017, 1-8.	0.3	0
20	Polarization Sensitive Reflection and Dielectric Spectra in GaSe Thin Films. <i>Advances in OptoElectronics</i> , 2016, 2016, 1-7.	0.6	1
21	Optical conduction in amorphous GaSe thin films. <i>Optik</i> , 2016, 127, 5193-5195.	2.9	10
22	MgO/GaSe<sub>0.5</sub>/S<sub>0.5</sub> Heterojunction as Photodiodes and Microwave Resonators. <i>IEEE Sensors Journal</i> , 2016, 16, 670-674.	4.7	1
23	Properties of Hf-Doped Bi<sub>1.5</sub>/Zn<sub>0.92</sub>/Nb<sub>1.5</sub>/O<sub>6.92</sub> Ceramic Varicaps. <i>IEEE Transactions on Electron Devices</i> , 2016, 63, 471-475.		3
24	Design and Applications of Al/InSe/BN/Ag Hybrid Device. <i>IEEE Sensors Journal</i> , 2015, 15, 3603-3607.	4.7	10
25	Analysis of the Junction Properties of C/GaSe<sub>0.5</sub>/S<sub>0.5</sub>/C Back-to-Back Schottky-Type Photodetectors. <i>IEEE Sensors Journal</i> , 2015, 15, 2269-2273.	4.7	3
26	Performance of the Au/MgO/Ni photovoltaic devices. <i>Materials Science in Semiconductor Processing</i> , 2015, 29, 183-187.	4.0	11
27	Fabrication and Characterization of Ag/BN/Ni Microwave Rejection-Band Filters. <i>IEEE Transactions on Electron Devices</i> , 2014, 61, 2154-2157.	3.0	3
28	Effects of Laser Excitation and Temperature on Ag/GaSe<sub>0.5</sub><sub>0.5</sub>/C Microwave Filters. <i>Journal of Electronic Materials</i> , 2014, 43, 3121-3127.	2.2	2
29	Investigations of 2.9-GHz Resonant Microwave-Sensitive Ag/MgO/Ge/Ag Tunneling Diodes. <i>Journal of Electronic Materials</i> , 2013, 42, 3451-3457.	2.2	3
30	Polarizing beam splitters for lightwave communication wavelengths using one-dimensional gaas grating layer embedded in GaP cube. , 2009, , .		1
31	Broadband IR polarizing beam splitter using a subwavelength-structured one-dimensional photonic-crystal layer embedded in a high-index prism. <i>Applied Optics</i> , 2009, 48, 5121.	2.1	12
32	Polarization properties of retroreflecting right-angle prisms. <i>Applied Optics</i> , 2008, 47, 359.	2.1	3
33	In-line broadband 270° (3π/4) chevron four-reflection wave retarders. <i>Applied Optics</i> , 2008, 47, 4878.	2.1	3